1. General description

The 74AUP2G34 provides two low-power, low-voltage buffers.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \ \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C





Ordering information 3.

Table 1. Orderi	ing information								
Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G34GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP2G34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891					

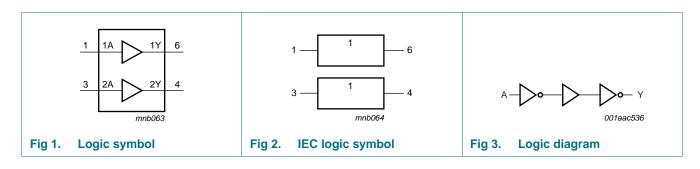
			6 terminals; body $1 \times 1 \times 0.5$ mm	
74AUP2G34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP2G34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202

Marking 4.

Table 2. Marking	
Type number	Marking code ^[1]
74AUP2G34GW	aA
74AUP2G34GM	aA
74AUP2G34GF	aA
74AUP2G34GN	aA
74AUP2G34GS	aA

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

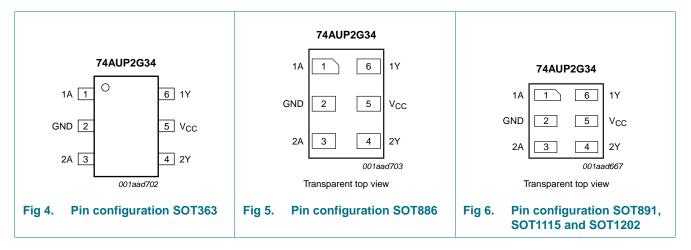
Functional diagram 5.



74AUP2G34 Product data sheet

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output
-		

7. Functional description

Table 4.Function table

Input	Output
	nY
L	L
Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

V_{CC} supply voltage0.83.6V V_I input voltage03.6V V_O output voltageActive mode0 V_{CC} V $Power-down mode; V_{CC} = 0 V$ 03.6V T_{amb} ambient temperature-40+125°C	Table 6.	Recommended operating condition	ons			
$ \begin{array}{ccc} V_{I} & \mbox{input voltage} & 0 & 3.6 & V \\ V_{O} & \mbox{output voltage} & \begin{tabular}{c} Active mode & 0 & V_{CC} & V \\ \hline Power-down mode; V_{CC} = 0 & V & 0 & 3.6 & V \\ \hline T_{amb} & \mbox{ambient temperature} & -40 & +125 & ^{\circ}C \\ \end{array} $	Symbol	Parameter	Conditions	Min	Max	Unit
V_O output voltageActive mode0 V_{CC} VPower-down mode; $V_{CC} = 0$ V03.6V T_{amb} ambient temperature-40+125°C	V _{CC}	supply voltage		0.8	3.6	V
Power-down mode; $V_{CC} = 0$ V03.6VT_{amb}ambient temperature-40+125°C	VI	input voltage		0	3.6	V
T_{amb} ambient temperature $-40 +125$ °C	Vo	output voltage	Active mode	0	V_{CC}	V
			Power-down mode; $V_{CC} = 0 V$	0	3.6	V
$\Delta t/\Delta V$ input transition rise and fall rate $V_{CC} = 0.8 V$ to 3.6 V - 200 ns/	T _{amb}	ambient temperature		-40	+125	°C
	$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

Table 6. Recommended operating conditions

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7$ mA; $V_{CC} = 3.0$ V	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	0.5	μΑ
∆l _{CC}	additional supply current		-	-	40	μΑ
CI	input capacitance	$V_{CC} = 0$ V to 3.6 V; $V_{I} = GND$ or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_0 = GND; V_{CC} = 0 V$	-	1.7	-	pF

Low-power dual buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = –	40 °C to +85 °C					
ViH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu\text{A};~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	$V_{\rm I}~or~V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V	-	-	±0.5	μΑ
\l _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
СС	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
7l ^{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μA

Table 7. Static characteristics ... continued

Low-power dual buffer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	-	-	$0.30\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I_{O} = –20 $\mu A;~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
√ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		I_{O} = 3.1 mA; V_{CC} = 2.3 V	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μΑ
∆I _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	1.4	μA
∆I _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μA

Table 7. Static characteristics ... continued



11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C			
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)		
C _L = 5 p	F		1							
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$	-	14.9	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.6	4.7	9.2	2.0	10.0	11.0	ns	
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.1	3.4	5.7	1.6	6.5	7.2	ns	
		V_{CC} = 1.65 V to 1.95 V	1.8	2.9	4.5	1.4	5.2	5.8	ns	
		V_{CC} = 2.3 V to 2.7 V	1.5	2.3	3.5	1.2	4.2	4.6	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.4	2.1	3.2	1.0	3.8	4.2	ns	
C _L = 10	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$	-	18.4	-	-	-	-	ns	
		V _{CC} = 1.1 V to 1.3 V	3.2	5.6	10.9	2.3	11.8	13.1	ns	
		V _{CC} = 1.4 V to 1.6 V	2.6	4.1	6.7	1.9	7.7	8.5	ns	
		V _{CC} = 1.65 V to 1.95 V	2.3	3.4	5.3	1.7	6.2	6.9	ns	
		V_{CC} = 2.3 V to 2.7 V	2.0	2.9	4.2	1.5	5.0	5.5	ns	
		V_{CC} = 3.0 V to 3.6 V	1.7	2.6	3.8	1.4	4.6	5.1	ns	
C _L = 15	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$	-	21.9	-	-	-	-	ns	
		V _{CC} = 1.1 V to 1.3 V	3.6	6.4	12.6	2.6	13.8	15.2	ns	
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	4.6	7.6	2.2	8.9	9.8	ns	
		V_{CC} = 1.65 V to 1.95 V	2.6	3.9	6.0	2.0	7.2	7.9	ns	
		V_{CC} = 2.3 V to 2.7 V	2.3	3.3	4.8	1.8	5.7	6.3	ns	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.1	3.1	4.2	1.6	5.0	5.5	ns	
C _L = 30	pF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$	-	32.1	-	-	-	-	ns	
		V _{CC} = 1.1 V to 1.3 V	4.8	8.7	16.3	3.6	18.9	20.8	ns	
		V_{CC} = 1.4 V to 1.6 V	4.0	6.2	10.3	3.4	12.2	13.4	ns	
		V_{CC} = 1.65 V to 1.95 V	3.6	5.2	8.1	3.2	9.8	10.8	ns	
		V_{CC} = 2.3 V to 2.7 V	3.0	4.4	6.4	2.7	7.7	8.5	ns	
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.9	4.2		2.5	6.5			

Low-power dual buffer

Unit

pF pF

pF

pF pF

pF

Voltages	are referenced to G	ND (ground = 0 V); for test circle	uit see	Figure	<u>8</u> .				
Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF							
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	<u>[3][4]</u>						
		$V_{CC} = 0.8 V$		-	2.5	-	-	-	-
		V_{CC} = 1.1 V to 1.3 V		-	2.6	-	-	-	-
		V_{CC} = 1.4 V to 1.6 V		-	2.7	-	-	-	-
		V_{CC} = 1.65 V to 1.95 V		-	2.9	-	-	-	-
		V_{CC} = 2.3 V to 2.7 V		-	3.4	-	-	-	-
		V_{CC} = 3.0 V to 3.6 V		-	4.0	-	-	-	-

Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_o) \text{ where:}$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

 C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

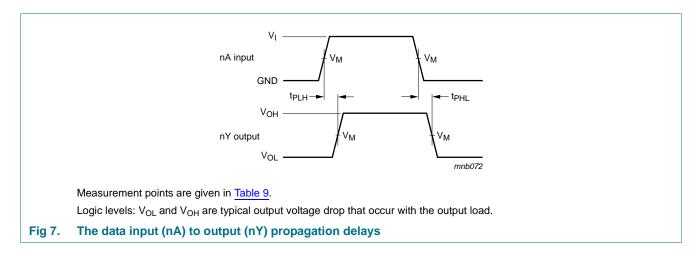


Table 9. **Measurement points**

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	V _{CC}	≤ 3.0 ns

74AUP2G34		
Product	data	sheet



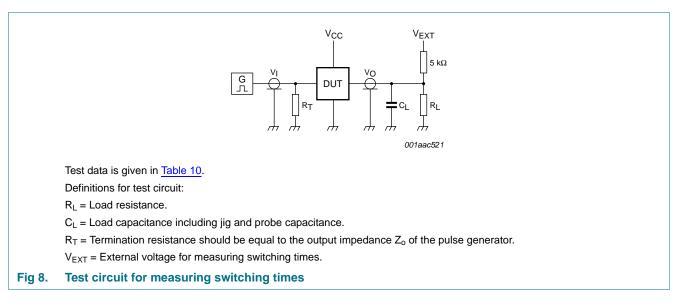


Table 10.Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Package outline

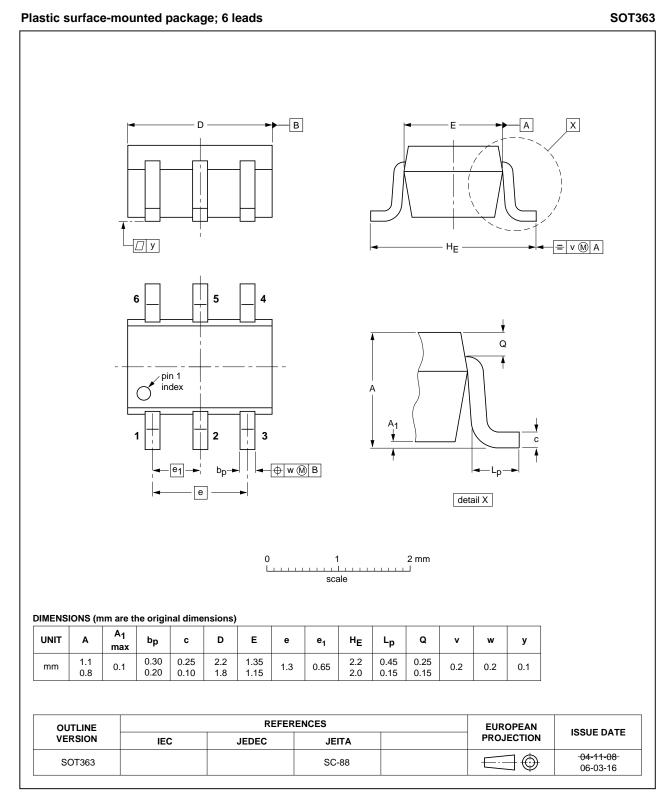
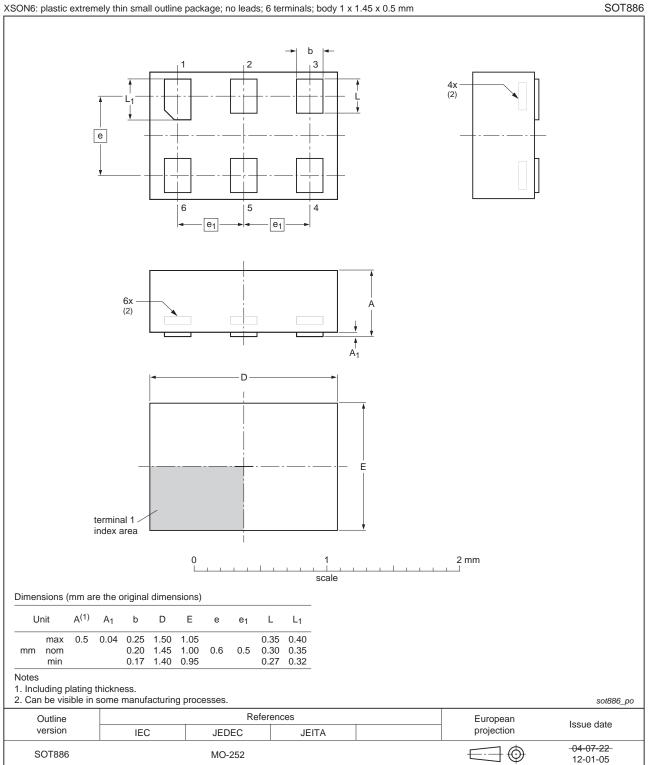


Fig 9. Package outline SOT363 (SC-88)

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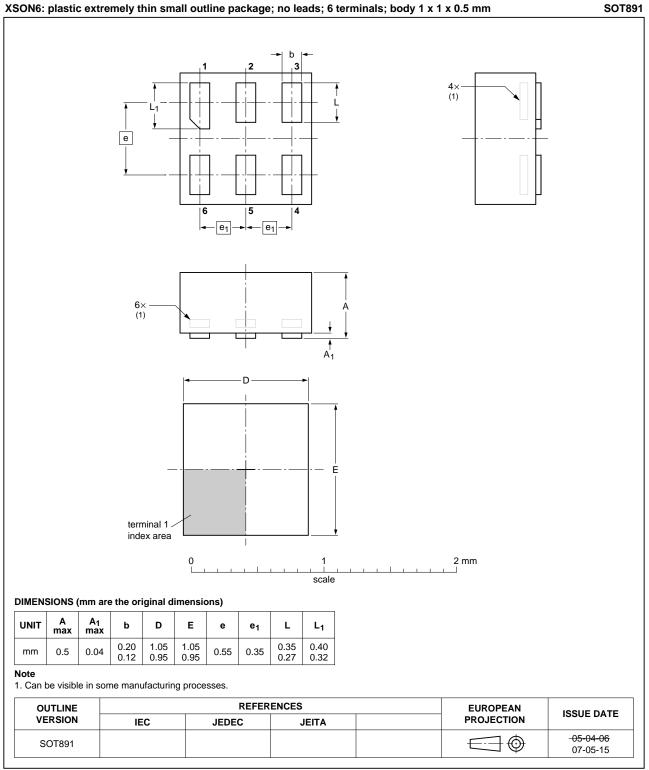




XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

Fig 10. Package outline SOT886 (XSON6)

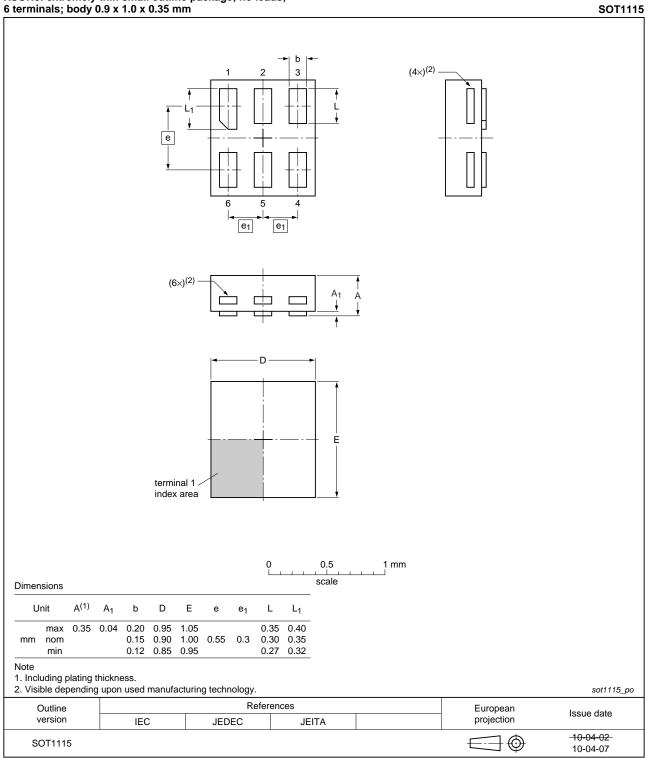
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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 11. Package outline SOT891 (XSON6)

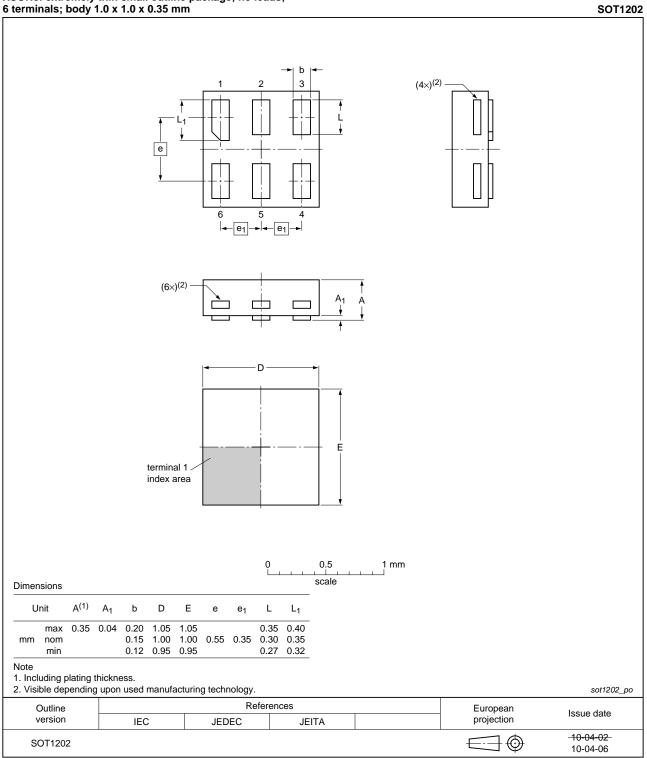
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 12. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1202 (XSON6)

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14. Abbreviations

AcronymDescriptionCDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model	Table 11. Abbreviations			
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model		Description	Acronym	
ESD ElectroStatic Discharge HBM Human Body Model		Charged Device Model	CDM	
HBM Human Body Model		Device Under Test	DUT	
		ElectroStatic Discharge	ESD	
		Human Body Model	HBM	
MM Machine Model		Machine Model	MM	

15. Revision history

Table 12. Revision history **Document ID Release date** Data sheet status **Change notice** Supersedes Product data sheet 74AUP2G34 v.5 20130110 74AUP2G34 v.4 Modifications: • Package outline drawing of SOT886 (Figure 10) modified. 74AUP2G34 v.4 20111206 Product data sheet 74AUP2G34 v.3 -Modifications: • Legal pages updated. 74AUP2G34 v.3 20100903 Product data sheet -74AUP2G34 v.2 74AUP2G34 v.2 20080131 Product data sheet 74AUP2G34 v.1 -74AUP2G34 v.1 20061122 Product data sheet _ _

16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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